



# MB8441-45/-55 CMOS 64K-BIT DUAL PORT SRAM

# 8K x 8-BIT CMOS DUAL PORT STATIC RANDOM ACCESS MEMORY

The Fujitsu MB8441 is an 8K words x 8 bits dual-port high-performance Static Random Access Memory (SRAM) fabricated in CMOS. The SRAM uses asynchronous circuitry and no external clocks are required. The MB8441 provide the user with two separately controlled VO ports with independent addresses, Chip Select (CS), Write Enable (WE), Output Enable (OE), and VO functions. This arrangement permits independent access to any memory location for either a Read or Write operation — a useful feature for shared data processing applications. These devices have an automatic power-down feature controlled by CS. The MB8441 can be used as either a master operation or slave operation by selecting the BE pin.

To avoid data contention on the same address, a (BUSY) flag is provided for address arbitration; in addition, the MB8441 utilizes an (INT) flag which allows communication between systems on either side of the RAM. The MB8441 uses a single 5-volt power supply and all pins are TTL-compatible.

Some typical applications for these memory devices are multiprocessing systems, distributed networks, external register files, and peripheral controllers.

#### **Features**

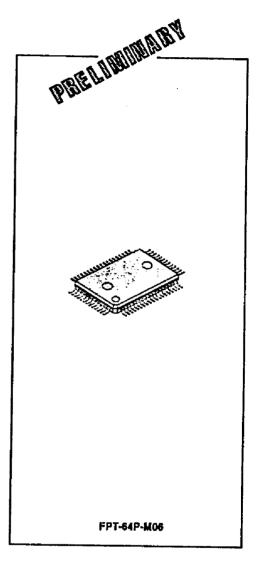
- Organization: 8,192 words x 8 bits.
- · Static operation: No clocks or timing strobes required.
- Access Time:

tAA = tACS = 45ns max. (MB8441-45) tAA = tACS = 55ns max. (MB8441-55)

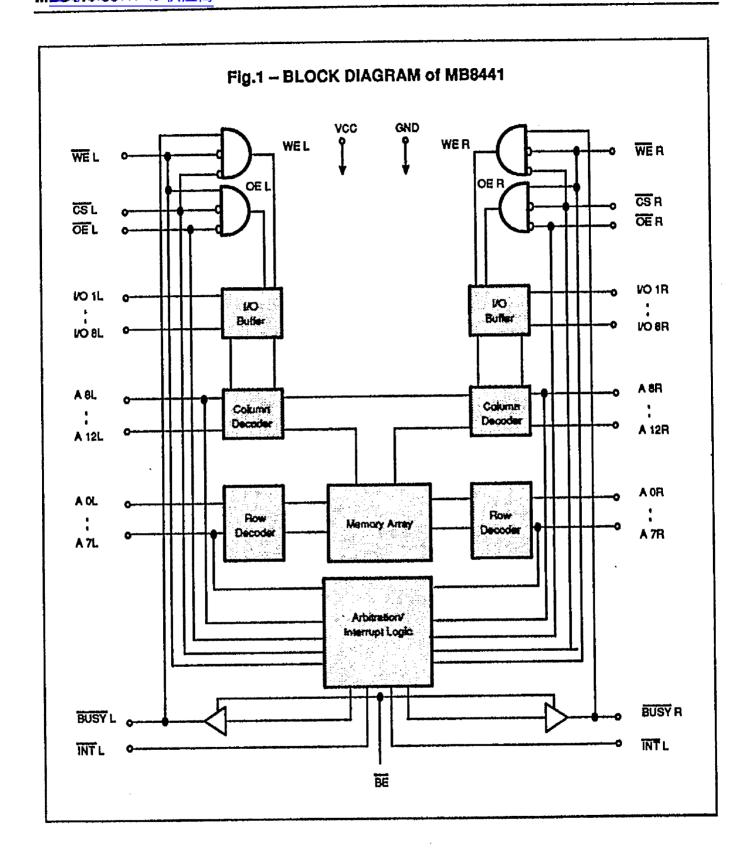
Power Consumption:

8oth ports active = 660 mW (max) Both ports standby CMOS = 1.1 mW (max) TTL = 27.5 mW (max)

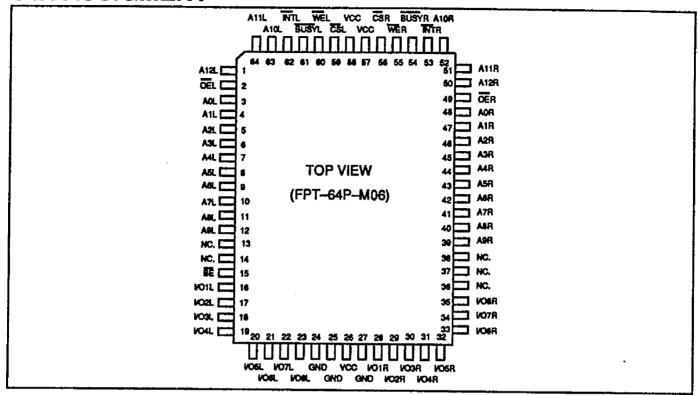
- TTL-compatible inputs and outputs.
- Three-state outputs with Or-tie capability.
- Electrostatic protection for all inputs and outputs.
- Addres arbitration: (BUSY) flag output (Master Operation: BE = "L")
   (BUSY) flag output (Slave Operation: BE = "H")
- Interrupt function for communication between systems: INT flag.
- Data retention voltage: 2.0V min.
- Single +5V (±10%) supply.
- 64-pin plastic quad flat package



This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.



# **PIN ASSIGMENT**



## **PIN DESCRIPTION**

Sy	mbol	170	
Left Part	Right Port	170	Function
CS L	CS R	ı	Chip select
WE L	WE R	1	Write enable
Œ L	ŌĒ R	ı	Output enable
A OL to A 12L	A 0R to A 12R	1	Address
I/O1L to I/O8L	I/O 1Rto I/O 8R	1/0	Data input / output
BUSYL	BUSY R	1/0	BUSY flag (BE = "L" : output, BE = "H" : input)
<del>INT</del> L	INTR	0	Interrupt output
	BE .	ı	BUSY output enable (Selects a Master or a Slave.)
V	CC	-	Supply voltage
G	GND		Ground
	IC.	_	No connection

## **FUNCTION DESCRIPTION**

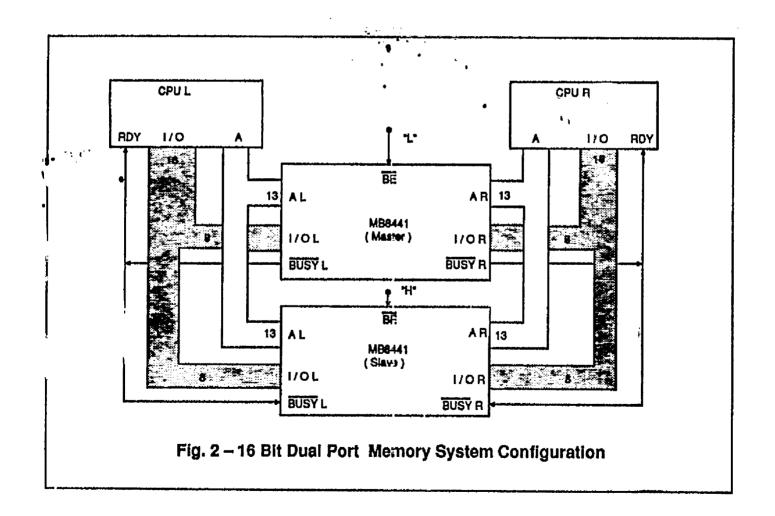
The MB8441 provides two ports with separate control signals, address inputs, and input/output data pins that allow asynchronous read and write operation to any memory location. This device has an on--chip automatic power--down feature controlled by  $\overline{CS}$  that places the respective port in the standby mode when the chip is deselected ( $\overline{CS}$  is HIGH). When a port is enabled, access to the entire memory array is permitted. Each port has an independent Output Enable ( $\overline{CS}$ ) control that is active in the read mode and enables the output drivers.

### **ARBITRATION LOGIC**

1. Master busy function ( BE = "L")

The arbitration logic resolves an address match or chip—enable match and determines the access priority. In both cases, an active BUSY flag is set for the port-in-waiting. Since both ports are asynchronous, there is the possibility of accessing the same memory location from both sides. In the read mode, this condition is not a problem. However, this is a problem when both ports are in the write mode with different data words or when one port is reading and the other is writing. When both ports access the same memory location, the on-chip arbitration logic determines which port has access and the BUSY flag for the delayed port is set active LOW and all operations on that port are inhibited. The delayed port can be accessed when the BUSY flag becomes inactive. Basic modes of abitration are described in subsequent paragraphs. (refer to timing diagram of "contention cycle".)

Access to delayed port is enabled as following, first set BUSY from "L" to "H" and then retain write mode (CS = WE = "L") during taw. BUSY signal dose not affect the read mode of delayed port normally. But in case that write operation is done from opposite port during BUSY signal output, read data may change. So it is recommended to read output data after t so passes from reset of BUSY signal.



### 2. Slave busy function ( BE = "H")

When the MB8441 is used with larger bit width than 8 bits, it is necessary to use more than two chips in paralell. In this case, each chip may output BUSY signal to other ports. It will be a problem if both CPU get BUSY signal. But the slave busy function can solve this problem. By this function, only the master chip operates the master busy function and the other chip obeys the master chip's BUSY signal. This function is operated by setting BE = "L" on one master chip and setting BE = "H" on the slave chips. By way of example, the composition of the 16 bit dual port memory system is showen in fig. 2.

In this system the master MB8441 with BE = "L" decides which port is first, and outputs the result to BUSY pin. This data is sent to the CPU and slave MB8441, then the CPU incurs the "wait" condition.

#### 3. Interrupt function

The interrupt (INT) function provides communication between systems on both sides of the dual-port RAM. INT is set to "L" when the processor on the right port writes to address 1FFE (A0 = "L" and A1-A12 = "H"). When the left port acknowledges by reading address 1FFE, INT is then reset to "H". In essence, address 1FFE serves as an 8-bit mailbox that transfers information from the right port to the left port. When INTR is set "L", the processor on the left port writes to address 1FFF (A0-A12="H"). When the right port acknowledges by reading address 1FFF, INTR is then reset to "H". Hence, address 1FFF serves as a second 8-bit mailbox, transferring information from the left port to the right port.

## ABSOLUTE MAXIMUM RATINGS

( All voltages are referenced to GND.)

Parameter	Symbol	Value	Unit
Supply Voltage	v cc	- 0.5 to + 7.0	٧
Input Voltage on any pin	VIN	- 0.5 to V CC + 0.5	V
Output Voltage on any pin	V NO	-0.5 to V CC +0.5	V
Output Current	IOUT	± 20	mA
Temperature under Bias	TA	10 to + 85	°C
Storage Temperature	T STG	- 40 to + 125	°c
Power Dissipation	PD .	1.0	w

#### Note:

Permanent device damage may occur if the above Absolute Maximum Ratings are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect device reliability

## RECOMMENDED OPERATING CONDITIONS

( All voltages are referenced to GND.)

Parameter	Symbol	Min	Тур	Max	Unit
Supply Voltage	v cc	4.5	5.0	5.5	v
Supply Voltage	GND		0		٧
Operating Temperature	TA	0		+ 70	°c

# **FUNCTION TABLE**

1. BASIC FUNCTION ( A OL to A12 L = A 0 R to A12 R)

Ľ	aft Port I		Rig	hi Port li	aput .	Function	
CS L	WEL	ŌE L	ČŠ A	WER	<b>Ö</b> ER		Supply Current
Н	Х	X	х	х	X	Left port standby	Standby
L	Н	Н	X	Х	Х	Left port output disable	Active
د	н	L	х	Х	x	Left port read	Active
L	L	X	x	х	x	Left port write	Active
Х	х	x	Н	х	x	Right port standby	Standby
X	х	X	L	н	Н	Right port output disable	Active
x	х	X	L	Н	L	Right port read	Active
х	Х	X	Ĺ.	L.	х	Right port write	Active

NOTES: X = Don't Care, L = Low, H = High

### 2. ARBITRATION FUNCTION (A 0 L to A12 L = A 0 R to A12 R)

BE		Left Port Input				Right Port Inpo		
DG		<b>ខន</b> ម	A OL 10 A 12 L	BUSYL	ĈŜ R	ADR WAIZR	BUSTA	Function
	٦	L	VBR	Н	L	Valid	L.	Left operation permitted
	ı	LBR	Match	H	L	Match	L	Right operation not permitted
Master	L	L	Valid	L	Ļ	VBL	Н	Right operation permitted
	L	L,	Match	L	LBL	Match	Н	Left operation not permitted
	L	L	VST		L	VST		
	L	LST	Match	•	LST	Match	•	•
Slave	Н	L	x	н	L.	x	L	Left operation permittee Right operation not permitted
J. A.	Н	L	x	L	L.	×	Н	Right operation permitted Left operation not permitted

X = Don't Care, L = Low, H = High, VBR = Valid Before Right, VBL = Valid Before Left, LBR = Low Before Right, LBL = Low Before Left, VST = Valid Same Time, LST = Low Same Time

In case that t APS (min.) is not satisfied, the on-chip arbitration logic decides which port has access. And the busy flag
for the delayed port is set "L" and all operations on that port are inhibited. But it is undefined which port has access or
not. ( Refer to timing diagram )

## DC CHARACTERISTICS

(Recommended Operating Conditions unless otherwise noted.)

Par <del>aenea</del>	air -	Symbol	Min	Тур.	Max	Unit	Condition
Operating Supply ( ( Both Port Activ	Current ve )	1 CÇ		_	120	mA	Cycle = min. Duty = 100%, I OUT = 0 mA
		I SB1	<del>  -</del>	_	5	mA	Both ports at Standby ; CSL & CSR = V IH
Standby Supply Current		I \$82	_	1	70	Αm	One port at Standby ; CSL or CSR = V iH, i OUT = 0 mA
		I SB3	_	-	0.2	mA	Both ports at Full Standby; CSL & CSR ≥ VCC = 0.2 V BE ≥ VCC = 0.2 V or BE ≤ GND + 0.2 V
		I SB4	_	-	70	mA	One port at Full Standby; CSL or CSR ≥ V CC - 0.2 V, I OUT ≈ 0 mA
Input Leakage Curr	rent	IU	-10		10	μА	V IN = GND to V CC
Output Leakage Cu	rrent	ILO	-10		10	μΑ	CS = VIH, VOUT = GND to VCC
Input High Voltage		VIH	2.2		V CC +	٧	
Input Low Voltage		VIL	-0.5	—	8.0	٧	
Output High Voltage		V OH	2.4			٧	I OH = -1.0 mA*2
	DOUT	VO		_	0.4	٧	I OL = 3.2 mA
Output Low Voltage	BUSY	VOL	_	-	0.4	٧	I OL = 8.0 mA

<sup>+1 -0.3</sup> V Min. for pulse width less than 20 ns.

# I/O CAPACITANCE (TA = 25°C, f = 1 MHz)

I / O Capacitance (V I/O = 0V)	c vo			10	ρF
Input Capacitance (VIN = 0V)	C IN	*****	_	· 10	ρF
Parameter	Symbol	Min.	Typ.	Max.	Unit

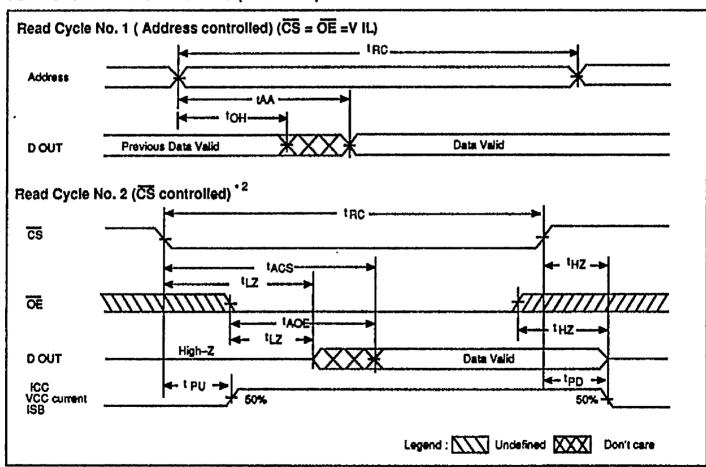
<sup>\*2</sup> The BUSY and INT pins require pull-up resistors because they are open-drain outputs.

# **AC CHARACTERISTICS**

READ CYCLE (Recommended operating conditions unless otherwisw noted.)

Parameter		MB8441-45			MB844			
	Symbol	Min	Тур.	Max	l <b>é</b> n	Тур.	Mex	Unit
Read Cycle Time	tRC	45			55			ns
Address Access Time	tAA			45			55	กร
CS Access Time	<sup>1</sup> ACS			45	_	-	55	ns
OE Access Time	IAOE			25		•	30	ns
Output Hold Time	tOH	3			3		_	N\$
CS to Output Low-Z *1	tÇLZ	3			3		_	ns
OE to Output Low-Z *1	tOLZ	3			3			ns
CS to Output High-Z*1	tCHZ		_	25	-		25	N\$
OE to Output High-Z*1	tOHZ			25	_		30	ns
Power Up Time	tPU	0			0			ns
Power Down Time	IPD			30	<b>4</b>	g-radia	40	n <b>s</b>

## READ CYCLE TIMING DIAGRAMS (WE = VIH)

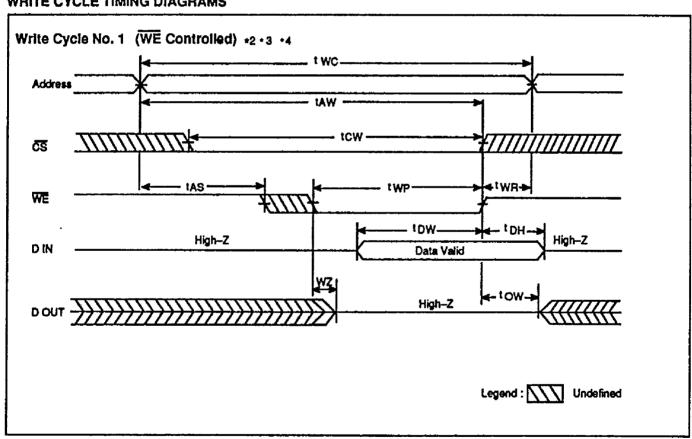


- \*1 :Transition is measured at the point of ± 500 mV from a steady state voltage with CL = 5 pF.
- •2: Address should be fixed before high-to-low transfer of CS.

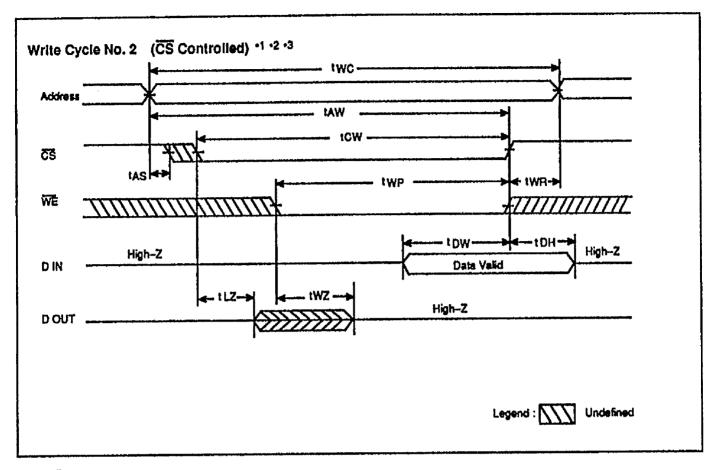
WRITE CYCLE (Recommended operating conditions unless otherwise noted.)

Parameter	Symbol		MB8441	45		MB8441-	-65	Unit	
ra alleto		Min	Тур.	Max	Min	Тур,	Max	<b>4</b> #	
Write Cycle Time	two	45			55			ns	
Address Valid to End of Write	tAW	40			50		_	п\$	
Chip Select to End of Write	tcw	40		-	50			ns	
Address Setup Time	tas	0		1	0	_		ns	
Write Pulse Width	t WP	25		_	35			ns	
Write Recovery Time	twn	0	_	_	0			ns	
Data Setup Time	t DW	20	_	1	25	_		ns	
Data Hold Time	¹ DH	0			0			กร	
WE to Output Low-Z *1	tow	0			0			ns	
WE to Output High-Z*1	t WZ	20	-		30			กร	

### WRITE CYCLE TIMING DIAGRAMS



- •1: Transition is measured at the point of ± 500 mV from a steady state voltage with CL = 5 pF.
- •2: WE must be high during address transition.
- \*3 : If OE and OS are in the READ Mode, I/O pins are in the output state so that the input signals of the opposite phase to the output must not be applied.
- •4: If CS goes high prior to, or coincidently with, WE transition to high, the output remains in high impedance state.



•1: WE must be high during address transition.

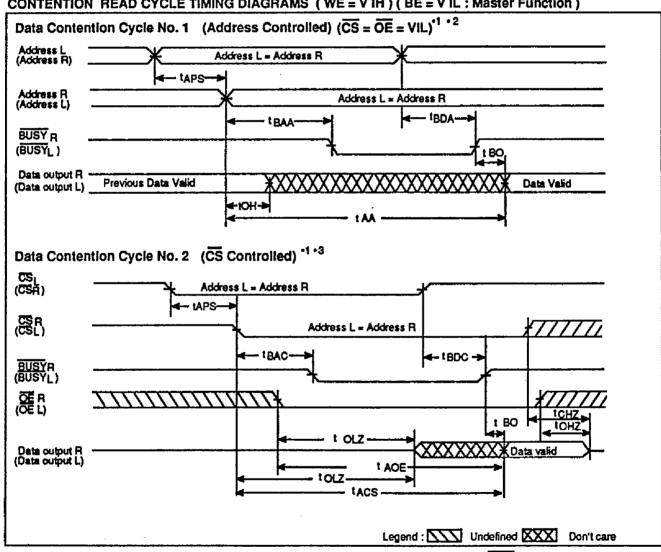
\*2 : If OE and CS are in the READ Mode, then I/O pins are in the output state so that the input signals of opposite phase to the output must not be applied.

•3 : If CS goes high prior to, or coincidently with, WE transition to high, the output remains in high impedance state.

### BUSY TIMING (BE = "L"; Master Function) ( Recommended operating conditions unless otherwise noted. )

Parameter	Symbol	Ţ	MB8441-45			8441-55	Unit	
Let en ideas	Symbol	Min	Тур	Max	Min	Тур	Max	O1#
BUSY Access Time from Address	t BAA		_	30			30	ns
BUSY Access Time from CS	t BAC			30			30	ns
BUSY Output High-Z from Address	t BDA			30			30	ns
BUSY Output High-Z from CS	t BDC			30			30	ns
Arbitration Priority Setup Time	t APS	5		_	5		_	ns
Data Output Access Time from BUSY	t BO			0			0	ns
Write Hold Time from BUSY	1 BW	25			35			ns

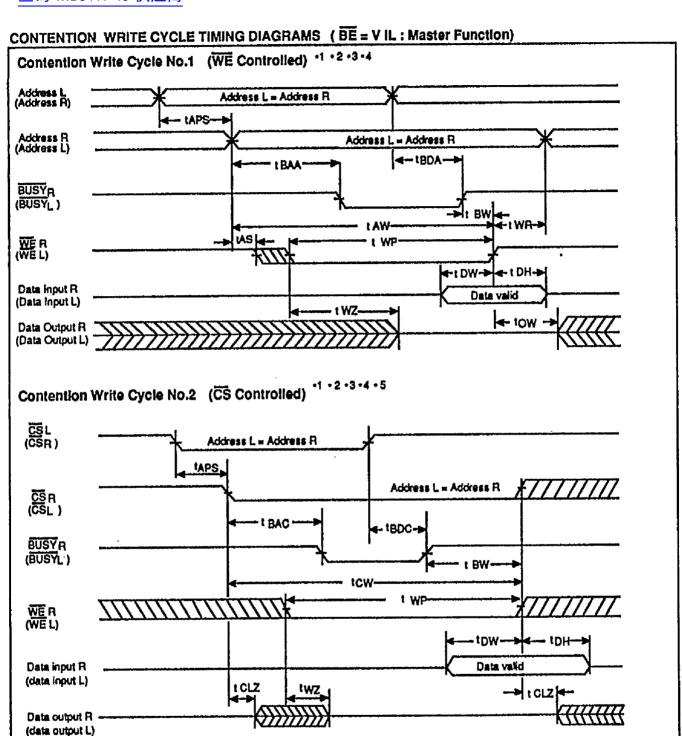
CONTENTION READ CYCLE TIMING DIAGRAMS (WE = VIH) (BE = VIL: Master Function)



<sup>• 1 :</sup> In case of dual access at the same memory location, the port that accesses the RAM first sets the BUSY flag high.

<sup>\* 2 :</sup> CS must be low before, or coincide with, transition of address.

<sup>\* 3 :</sup> Address is valid prior to, or coincidently with, high-to-low transition of CS.



<sup>-1 :</sup> WE must be high during address transition.

Legend : Undefined

<sup>• 2 :</sup> If OE and CS are in the READ Mode, then I/O pins are in the output state, and the input signals of opposite phase to the outputs must not be applied.

<sup>•3 :</sup> in case of dual access at the same memory location, the port that accesses the RAM first sets the BUSY flag high.

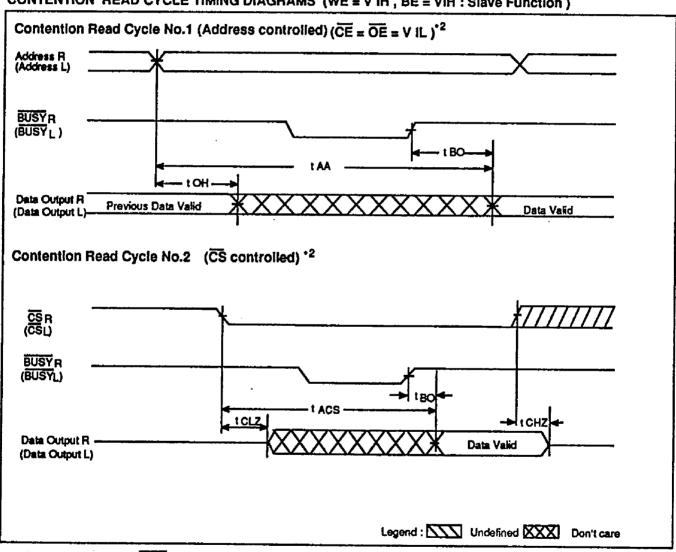
<sup>•4:</sup> CS must be low before, or coincide with, transition of CS.

<sup>• 5 :</sup> If CS goes high prior to, or coincidently with, WE transition to high, the output remains in high impedance.

BUSY TIMING (BE = "H"; Slave Function)
(Recommended operating conditions unless otherwise noted.)

P. J.	_	MB8441-45				MB8441-5		
Parameter	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Data Output Access Time from BUSY	t BO		_	0	_	_	0	ns
Write Setup Time to BUSY 1	t WS	-10	_	_	-10		_	ns
Write Hold Time from BUSY	t WH	25		_	35	-	_	ns

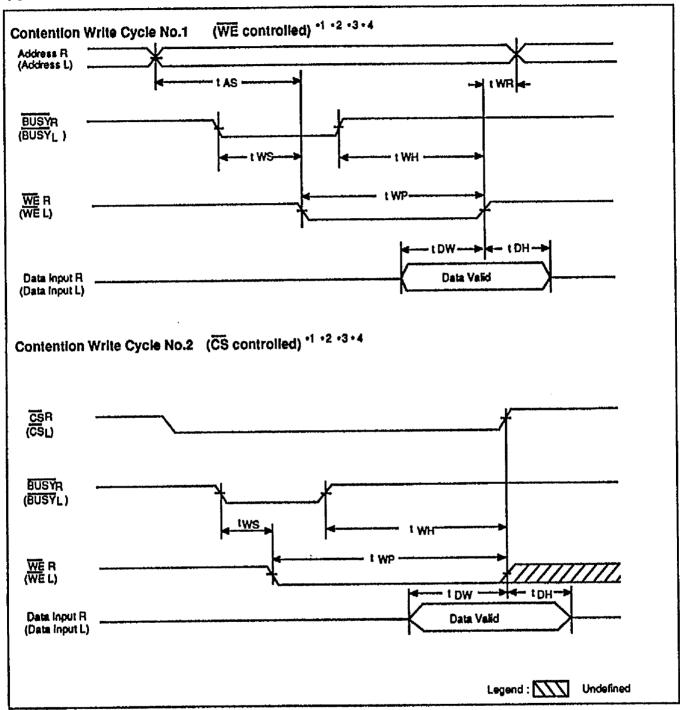
CONTENTION READ CYCLE TIMING DIAGRAMS (WE = V IH, BE = VIH : Slave Function )



<sup>•1:</sup> It takes 30 ns to output BUSY signal from the master side, and so, the tAS (address set up time) of the slave side must be 20 ns or more.

<sup>•2:</sup> CS must be low before, or coincide with, transition of address.

# CONTENTION WRITE CYCLE TIMING DIAGRAMS ( BE = V IH : Slave Function)

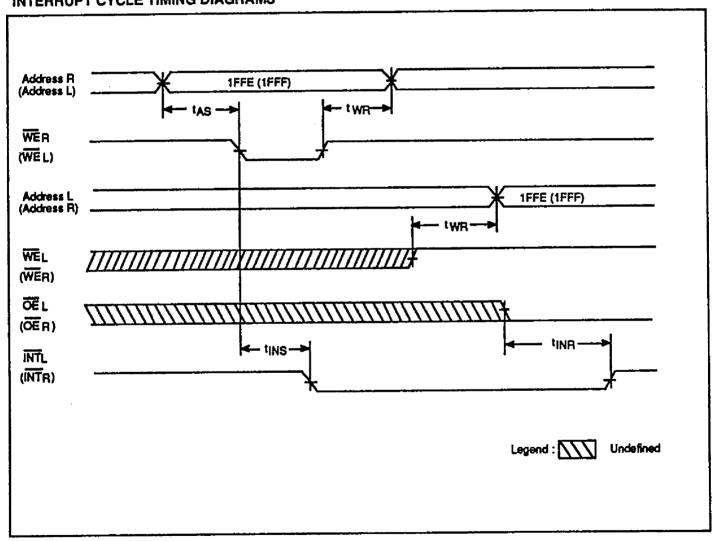


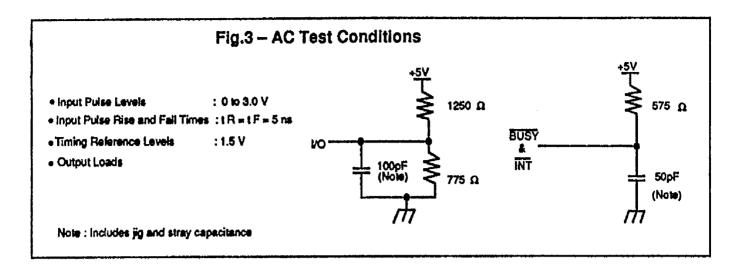
- •1: WE must be high during address transition.
- •2 : VO pins are in the output state, so the input signals of opposite phase must not be applied.
- •3 : CS must be low before, or coincide with, transition of address.
- \*4 : During BUSY input is low, write operation can not be excuted even if WE is low.

INTERRUPT TIMING ( Recommended operating conditions unless otherwise noted. )

INT Reset Time	tINR	-		45	_		55	ns
INT Set Time	t INS	_		45	-	_	55	ns
Parameter	Symbol	Min.	VB8441	I5 Max.	Min.	ИВ8441⊷ Тур.	Max.	Unit

## INTERRUPT CYCLE TIMING DIAGRAMS



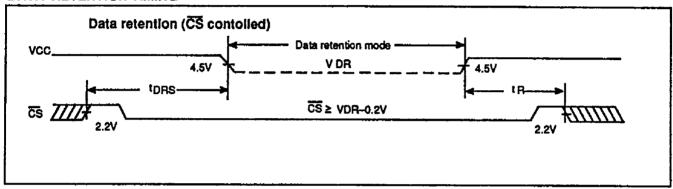


## **DATA RETENTION CHARACTERISTICS**

( Recommended operating conditions unless otherwise noted.)

Parameter	Symbol	Min.	Max,	Unit	Condition
Data Retention Supply Voltage	VDR	2.0	5.5	۷,	
Data Retention Supply Current	IDR		0.02	mA	V CC = V DR = 3V CSL & CSR ≥ V CC0.2V, BE ≥ VCC 0.2 V or BE≤ GND + 0.2 V
Data Retention Setup Time	t DRS	0		កន	
Operation Recovery Time	tR	t RC	_	N\$	

### **DATA RETENTION TIMING**

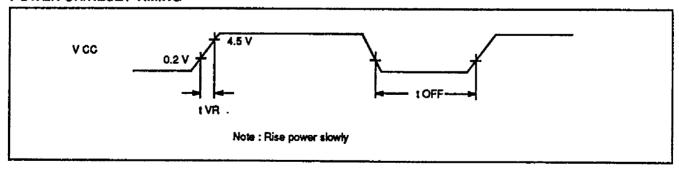


# **POWER ON/RESET CHARACTERISTICS**

(Recommended operating conditions unless otherwise noted.)

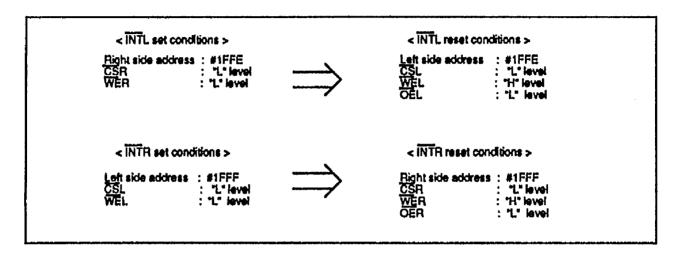
Power Off Time	t OFF	1		\$
Rising Time of Supply Voltage*1	t VR	0.05	50	ms
Parameter	Symbol	Nin.	Max.	Unit

### **POWER ON/RESET TIMING**

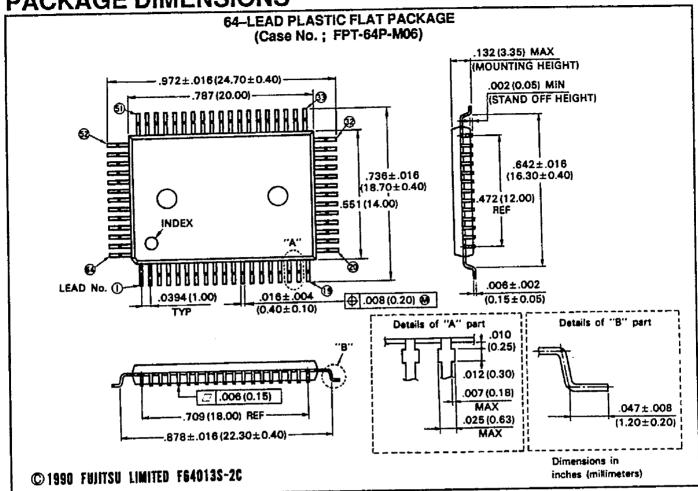


Note:

11: This is required to keep normal operation for the power on/reset circuit which initialize INT output to "H" automatically when Vcc is applied, in order to operate power-on-reset circuit normally, input conditions to set INT (refer to below) must not be applied during tVR period. And when input conditions are undefined during tvn period, INT may be set. So it is necessary to reset with a dummy read (refer to below).



# **PACKAGE DIMENSIONS**



#### All Rights Reserved.

Circuit diagrams utilizing Fujitsu products are included as a means of illustrating typical semiconductor applications. Complete Information sufficient for construction purposes is not necessarily given.

The information contained in this document has been carefully checked and is believed to be reliable. However, Fujitsu assumes no responsibility for inaccuracies.

The information contained in this document does not convey any license under the copyrights, patent rights or trademarks claimed and owned by Fujitsu.

Fujitsu reserves the right to change products or specifications without notice.

No part of this publication may be copied or reproduced in any form or by any means, or transferred to any third party without prior written consent of Fujitsu.